ESD5B5.0ST1G
Bi-direction ESD Protection Diode

Description

Designed to protect voltage sensitive electronic components from ESD and other transients. Excellent clamping capability, low leakage, low capacitance, and fast response time provide best in class protection on designs that are exposed to ESD.

The combination of small size, low capacitance, and high level of ESD protection makes them a flexible solution for applications such as HDMI, Display Port TM, and MDDI interfaces. It is designed to replace multiplayer varistors (MLV) in consumer equipments applications such as mobile phone, notebook, PAD, STB, LCD TV etc.

Applications

Computers and peripherals

High speed data lines

Audio and video equipment

Cellular handsets and accessories

Subscriber identity module(SIM) card protection

Portable electronics

FireWire

Other electronics equipments communi- cation systems

Features

Bi-directional ESD protection of one line

Reverse stand−off voltage:5 V

Low reverse clamping voltage

Low leakage current

Fast response time

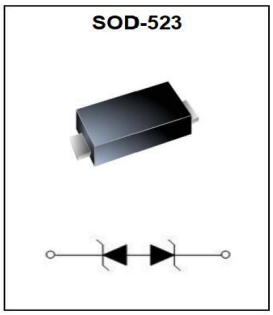
IEC 61000-4-2 (ESD) immunity test：

Air discharge: ±30kV

Contact discharge: ±30kV

5B

SOD-523



Absolute Maximum Rating

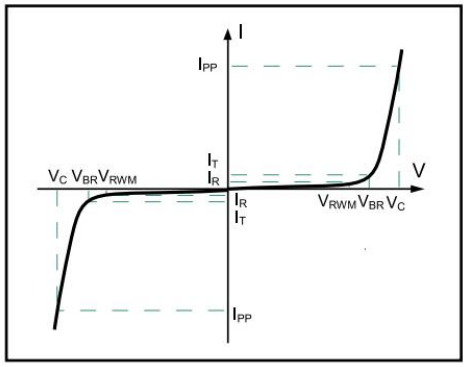
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	80	W
Peak Pulse Current (8/20μs)	IPP	8	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	TJ	−55to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics

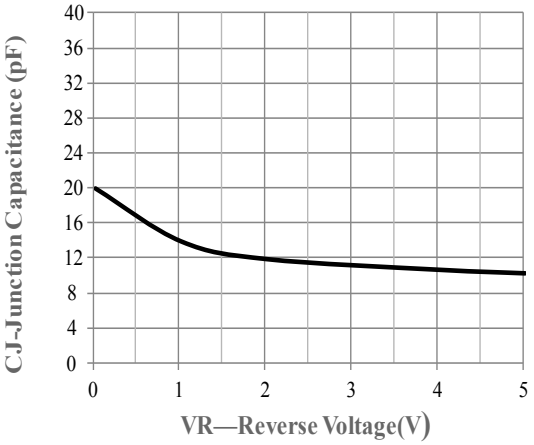
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	VR_{WM}				5	V
Breakdown Voltage	VB	I_T = 1mA	5.6		8	V
Reverse Leakage Current	IR	VR_{WM} = ±3.3V			0.1	uA
Clamping Voltage	Vc	I_{PP} = 8A (8 x 20μs pulse)			11	V
Junction Capacitance	Cj	VR = 0V, f = 1MHz			20	pF

Electronics Parameter

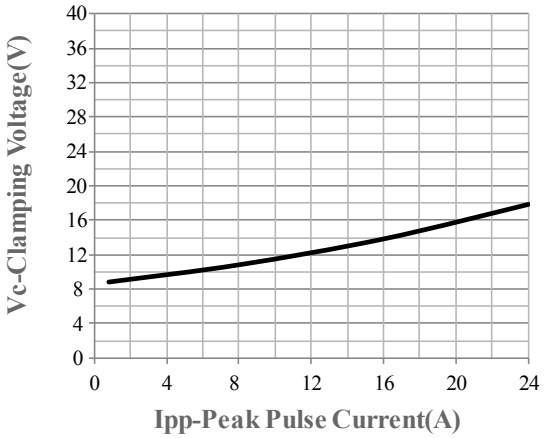
Symbol	Parameter
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @Ic
V_{BR}	Breakdown Voltage @ IT
I_R	Reverse Leakage Current @ VRWM
V_{RWM}	Reverse Standoff Voltage



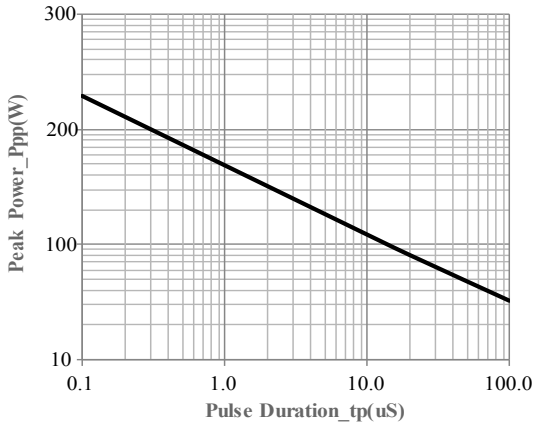
RATING AND CHARACTERISTIC CURVES



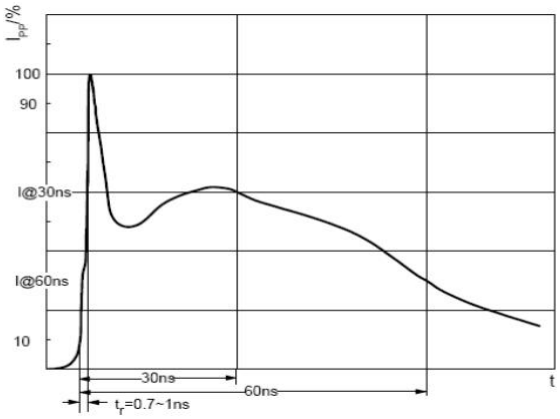
Junction Capacitance vs. Reverse Voltage



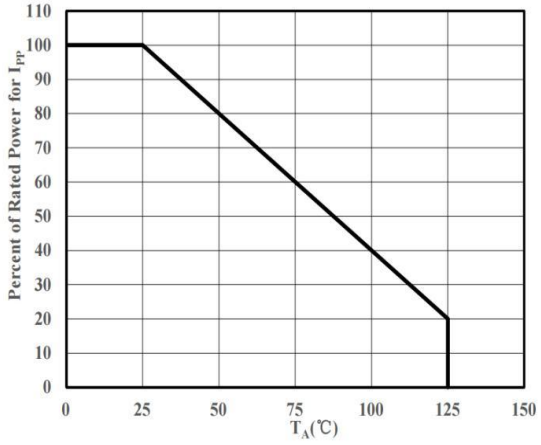
Clamping Voltage vs. Peak Pulse Current



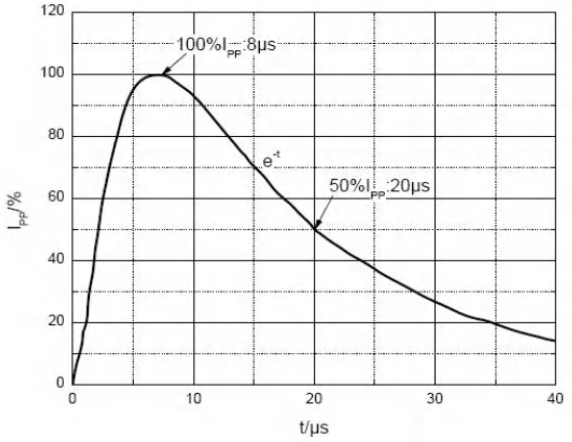
Peak Pulse Power vs. Pulse Time



ESD pulse waveform according to IEC61000-4-2



Power Derating Curve

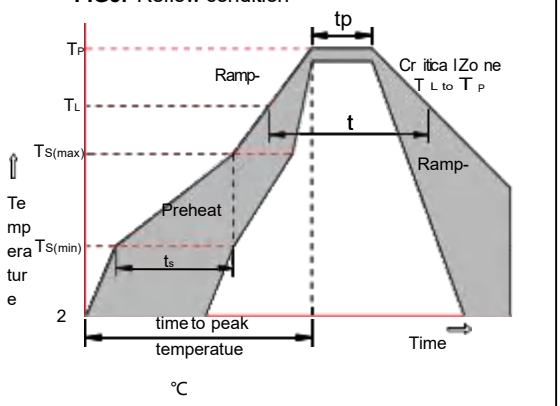


8/20μs pulse waveform according to IEC 61000-4-5

Soldering parameters

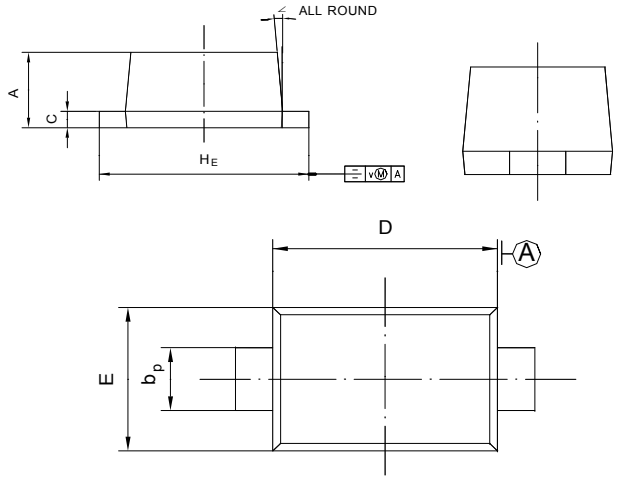
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

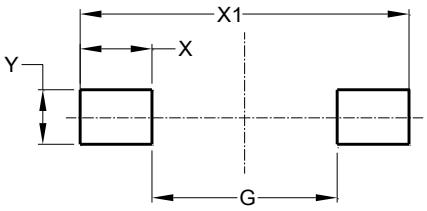


Package Dimensions & Suggested Pad Layout

SOD523



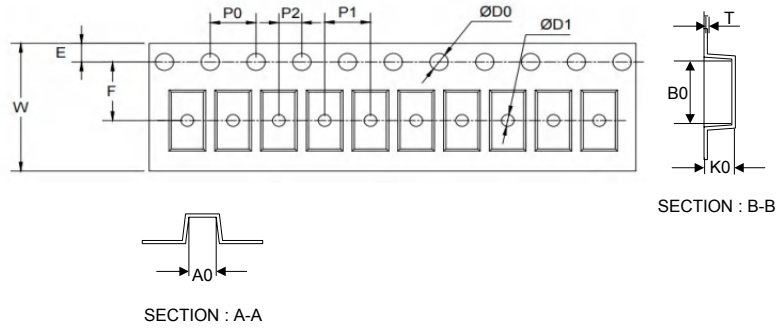
UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.50	0.40 0.20	0.14 0.05	1.30 1.10	0.90 0.75	1.70 1.50	0.1	5°



Dimensions	Value (in mm)
G	0.85
X	0.70
X1	2.25
Y	0.80

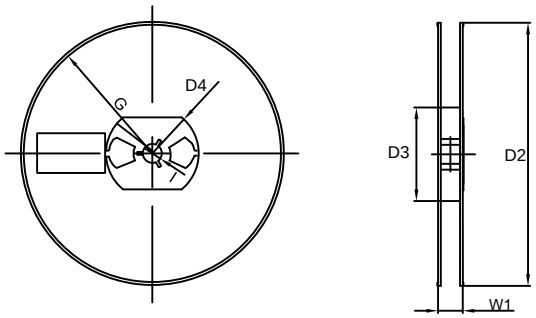
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	2.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	0.50±0.20
E	1.55±0.25
F	3.60±0.20
W	8.00±0.20
A0	1.30±0.20
B0	2.35±0.20
K0	0.95±0.20
T	0.20±0.20

7” Reel



D2	177.0±5.0
D3	55Min.
D4	R24.6±2.0
G	R82.0±2.0
I	13.0±2.0
W1	10.20±3.0

Quantity: 3000PCS